

# **isc** Silicon NPN Darlington Power Transistor

## 2SD2449

#### DESCRIPTION

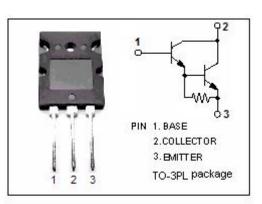
- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 160V(Min)
- High DC Current Gain-
- :  $h_{FE}$ = 3000( Min.) @(I<sub>C</sub>= 8A, V<sub>CE</sub>= 5V)
- Low Collector Saturation Voltage-
- :  $V_{CE(sat)}$  3.0V(Max)@ (I<sub>C</sub>= 8A, I<sub>B</sub>= 8mA)
- Complement to Type 2SB1594
- Minimum Lot-to-Lot variations for robust device
  performance and reliable operation

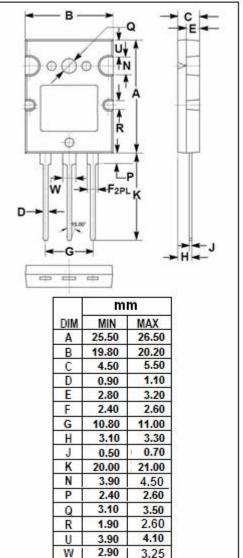
## APPLICATIONS

• Designed for power amplifier applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
lc	Collector Current-Continuous	10	A
IB	Base Current-Continuous	1	A
Pc	Collector Power Dissipation @Tc=25℃	150	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C







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## **ELECTRICAL CHARACTERISTICS**

#### Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	Ic= 50mA ; Iв= 0	160			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 8mA			3.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V			3.0	V
I <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = 160V; I <sub>E</sub> = 0			100	μA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 160V; I <sub>B</sub> = 0			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V	3000		20000	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 12A; V <sub>CE</sub> = 5V	2000			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		30		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		150		pF

#### • h<sub>FE-1</sub> Classifications

A	В	с
3000-10000	5000-15000	7000-20000

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